L Number	Hits	Search Text	DB	Time stamp
1	11242	((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103) or (372/4$1) or (372/50)).CCLS.	USPAT; US-PGPUB	2004/11/07 13:26
2	72	(((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103) or (372/4$1) or (372/50)).CCLS.) and (dual adj dopant window adj layer) and (transparent near3 oxide ZnO ITO)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 13:44
3	41	((((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103) or (372/4$1) or (372/50)).CCLS.) and (dual adj dopant window adj layer) and (transparent near3 oxide ZnO ITO)) and (dual$2 dopant doping impurities impurity) and (transparent near3 oxide ZnO ITO)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 13:46
4	0	epistar.as. and oxide.clm. and window.clm. and dual$2.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 13:48
5	0	epistar.as. and oxide.clm. and dual$2.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 13:48
6	0	epistar.as. and dual$2.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 13:48
7	0	epistar.as. and dual.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 13:49
8	5	epistar.as. and (light adj emitting light-emitting).clm. and contact adj (film layer).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 13:50
—	3	605513.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 13:08
—	99	"5563422"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 11:49
—	2	("5563422").PN.	USPAT; DERWENT	2004/11/04 11:50
—	2	("6078064").PN.	USPAT; DERWENT	2004/11/04 11:51
—	15	dual adj contact and (light-emitting light adj emitting laser).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 11:57
—	968	(contact near4 n-type near4 p-type) and (light-emitting light adj emitting laser).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 11:57
—	613	(contact near3 n-type near3 p-type) and (light-emitting light adj emitting laser).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 11:58

–	239	(contact near2 n-type near2 p-type) and (light-emitting light adj emitting laser).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 12:09
–	3	dual adj doping and (light-emitting light adj emitting laser).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 12:19
–	56919	contact.ti,ab,clm. and (light-emitting light adj emitting laser).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 12:20
–	4506	contact.ti,ab,clm. and (light-emitting light adj emitting laser).ti,ab,clm. and (257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. 372/43.ccls. 372/44.ccls. 372/45.ccls. 372/46.ccls. 372/47.ccls. 372/48.ccls. 372/49.ccls. 372/50.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 12:21
–	94	contact.ti,ab,clm. and (light-emitting light adj emitting laser).ti,ab,clm. and (257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. 372/43.ccls. 372/44.ccls. 372/45.ccls. 372/46.ccls. 372/47.ccls. 372/48.ccls. 372/49.ccls. 372/50.ccls.) and (brightness light adj intensity).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 12:43
–	31	contact.ti,ab,clm. and (light-emitting light adj emitting laser).ti,ab,clm. and (257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. 372/43.ccls. 372/44.ccls. 372/45.ccls. 372/46.ccls. 372/47.ccls. 372/48.ccls. 372/49.ccls. 372/50.ccls.) and (brightness light adj intensity).ti,ab,clm. and contact near4 (dual n-type p-type)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 14:14
–	0	540/145/ccls. and semiconductor and porphyrin	USPAT	2004/11/04 14:31
–	17	540/145.ccls. and semiconductor and porphyrin	USPAT	2004/11/04 14:34
–	3	396512.ap.	USPAT	2004/11/04 14:52
–	4	396512.ap.	USPAT; US-PGPUB	2004/11/04 14:53
–	5809	((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS.	USPAT; US-PGPUB	2004/11/07 13:25
–	1142	(((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS.) and (sapphire "Al.sub.2"$1"O.sub.3" "LiGaO.sub.2" "LiAlO.sub.2") near4 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 16:31
–	5	(((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS.) and (sapphire "Al.sub.2"$1"O.sub.3" "LiGaO.sub.2" "LiAlO.sub.2") near4 substrate and buffer near4 AlInGaN and (MQW multiple adj quantum adj well) and (transparent adj electrode oxide zinc adj2 oxide ITO indium-tin-oxide indium adj tin adj oxide indium-tin adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 16:51
–	6	(US-5563422-$ or US-6078064-$ or US-6207972-$).did. or (US-20040104399-$).did. or (EP-622858-$ or US-6078064-$).did.	USPAT; US-PGPUB; DERWENT	2004/11/04 16:48

–	5	(((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS.) and (sapphire "Al.sub.2"$1"O.sub.3" "LiGaO.sub.2" "LiAlO.sub.2") near4 substrate and buffer near4 AlInGaN and (MQW multiple adj quantum adj well) and (transparent adj electrode oxide zinc adj2 oxide ITO indium-tin-oxide indium adj tin adj oxide indium-tin adj oxide oxide near4 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 16:53
–	183	(((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS.) and (sapphire "Al.sub.2"$1"O.sub.3" "LiGaO.sub.2" "LiAlO.sub.2") near4 substrate and buffer near4 (GaN InN AlN AlInGaN) and (MQW multiple adj quantum adj well) and (transparent adj electrode oxide zinc adj2 oxide ITO indium-tin-oxide indium adj tin adj oxide indium-tin adj oxide oxide near4 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 16:53
–	185	(((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS.) and (sapphire "Al.sub.2"$1"O.sub.3" "LiGaO.sub.2" "LiAlO.sub.2") near4 substrate and buffer near4 (GaN InN AlN AlInGaN GaInN InGaN AlGaN GaAlN AlInN InAlN) and (MQW multiple adj quantum adj well) and (transparent adj electrode oxide zinc adj2 oxide ITO indium-tin-oxide indium adj tin adj oxide indium-tin adj oxide oxide near4 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 16:54
–	3	(((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS.) and (sapphire "Al.sub.2"$1"O.sub.3" "LiGaO.sub.2" "LiAlO.sub.2") near4 substrate and buffer near4 (GaN InN AlN AlInGaN GaInN InGaN AlGaN GaAlN AlInN InAlN) and (MQW multiple adj quantum adj well) and (transparent adj electrode oxide zinc adj2 oxide ITO indium-tin-oxide indium adj tin adj oxide indium-tin adj oxide oxide near4 electrode) and dual	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 16:55
–	1	(((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS.) and (sapphire "Al.sub.2"$1"O.sub.3" "LiGaO.sub.2" "LiAlO.sub.2") near4 substrate and buffer near4 (GaN InN AlN AlInGaN GaInN InGaN AlGaN GaAlN AlInN InAlN) and (MQW multiple adj quantum adj well) and (transparent adj electrode oxide zinc adj2 oxide ITO indium-tin-oxide indium adj tin adj oxide indium-tin adj oxide oxide near4 electrode) and dual near4 contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 16:55
–	0	(((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS.) and (sapphire "Al.sub.2"$1"O.sub.3" "LiGaO.sub.2" "LiAlO.sub.2") near4 substrate and buffer near4 (GaN InN AlN AlInGaN GaInN InGaN AlGaN GaAlN AlInN InAlN) and (MQW multiple adj quantum adj well) and (transparent adj electrode oxide zinc adj2 oxide ITO indium-tin-oxide indium adj tin adj oxide indium-tin adj oxide oxide near4 electrode) and dual near4 doping	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/04 16:56

-	467	multiple adj quantum adj well.ti,ab,clm. and (light-emitting light adj emitting).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 14:02
-	24	multiple adj quantum adj well.ti,ab,clm. and (light-emitting light adj emitting).ti,ab,clm. and barrier adj layer near6 "well layers"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 09:13
-	9	(US-6207972-$ or US-6078064-$ or US-5563422-$).did. or (US-20040056258-$ or US-20020197764-$ or US-20040164310-$ or US-20040104399-$).did. or (EP-622858-$ or US-6078064-$).did.	USPAT; US-PGPUB; DERWENT	2004/11/05 13:50
-	5	"6207972"	USPAT; US-PGPUB; DERWENT	2004/11/05 13:51
-	2	6207972.pn.	USPAT; US-PGPUB; DERWENT	2004/11/05 13:51
-	1	multiple adj quantum adj well.ti,ab,clm. and (light-emitting light adj emitting).ti,ab,clm. and buffer near5 substrate and (conductive oxide ZnO ITO indium-zinc adj oxide) and (dual near3 (dopant doped)) and (GaN SiC silicon Ge germanium AlN GaAs InP GaP) near4 substrate and buffer near5 (AlInGaN InGaAlN AlGaInN InAlGaN GaAlInN GaInAlN AlN InN GaN AlGaN GaAlN InGaN GaInN AlInN InAlN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 14:08
-	42	multiple adj quantum adj well.ti,ab,clm. and (light-emitting light adj emitting).ti,ab,clm. and buffer near5 substrate and (conductive oxide ZnO ITO indium-zinc adj oxide) and (GaN SiC silicon Ge germanium AlN GaAs InP GaP) near4 substrate and buffer near5 (AlInGaN InGaAlN AlGaInN InAlGaN GaAlInN GaInAlN AlN InN GaN AlGaN GaAlN InGaN GaInN AlInN InAlN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 18:46
-	30	multiple adj quantum adj well.ti,ab,clm. and (light-emitting light adj emitting).ti,ab,clm. and buffer near5 substrate and (conductive oxide ZnO ITO indium-zinc adj oxide) and (GaN SiC silicon Ge germanium AlN GaAs InP GaP) near4 substrate and buffer near5 (AlInGaN InGaAlN AlGaInN InAlGaN GaAlInN GaInAlN AlN InN GaN AlGaN GaAlN InGaN GaInN AlInN InAlN) and (clad cladding)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 16:35
-	120	(light-emitting light adj emitting laser).ti,ab,clm. and (buffer near6 GaAs near6 AlGaInP)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 17:19
-	23	(light-emitting light adj emitting laser).ti,ab,clm. and (buffer near3 GaAs near3 AlGaInP)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 16:39
-	44	(light-emitting light adj emitting laser).ti,ab,clm. and ((clad cladding) near6 buffer near6 GaAs near6 AlGaInP near6 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 16:40

–		44	((light-emitting light adj emitting laser).ti,ab,clm. and ((clad cladding) near6 buffer near6 GaAs near6 AlGaInP near6 substrate)) and ((clad cladding) near6 buffer near6 GaAs near6 AlGaInP near6 substrate).	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 16:43
–		14	((light-emitting light adj emitting laser).ti,ab,clm. and ((clad cladding) near6 buffer near6 GaAs near6 AlGaInP near6 substrate)) and ((clad cladding) near6 buffer near6 GaAs near6 AlGaInP near6 substrate) and (transparent adj2 oxide zinc oxide ZnO indium-tin adj oxide ITO)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 16:45
–		8	((light-emitting light adj emitting laser).ti,ab,clm. and ((clad cladding) near6 buffer near6 GaAs near6 AlGaInP near6 substrate)) and ((clad cladding) near6 buffer near6 GaAs near6 AlGaInP near6 substrate) and (transparent adj2 oxide zinc adj oxide ZnO indium-tin adj oxide ITO)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 17:45
–		1	((light-emitting light adj emitting laser).ti,ab,clm. and ((clad cladding) near6 buffer near6 GaAs near6 AlGaInP near6 substrate)) and ((clad cladding) near6 buffer near6 GaAs near6 AlGaInP near6 substrate) and (transparent adj2 oxide zinc adj oxide ZnO indium-tin adj oxide ITO) and (MQW multiple adj quantum adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 16:48
–		2	5233204.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 18:26
–		29	p-type adj electrode near3 "formed".clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 18:27
–		53	multiple adj quantum adj well.ti,ab,clm. and (light-emitting light adj emitting).ti,ab,clm. and buffer near5 substrate and (GaN SiC silicon Ge germanium AlN GaAs InP GaP) near4 substrate and buffer near5 (AlInGaN InGaAlN AlGaInN InAlGaN GaAlInN GaInAlN AlN InN GaN AlGaN GaAlN InGaN GaInN AlInN InAlN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 18:47
–		11	multiple adj quantum adj well.ti,ab,clm. and (light-emitting light adj emitting).ti,ab,clm. and buffer near5 substrate and (GaN SiC silicon Ge germanium AlN GaAs InP GaP) near4 substrate and buffer near5 (AlInGaN InGaAlN AlGaInN InAlGaN GaAlInN GaInAlN AlN InN GaN AlGaN GaAlN InGaN GaInN AlInN InAlN) and buffer.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 18:48
–		1	5981977.pn. and (MQW multiple adj quantum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 13:13
–		0	active near4 InGaN near4 GaN near4 (MQW multiple adj quantum) near4 efficiency	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 13:13

-	0	active near8 InGaN near8 GaN near8 (MQW multiple adj quantum) near8 efficiency	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 13:14
-	68	active near8 (MQW multiple adj quantum) near8 efficiency	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 13:14
-	3	active near4 (MQW multiple adj quantum) near4 efficiency and InGaN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 13:52
-	192	active near4 (MQW multiple adj quantum) near12 InGaN and buffer and substrate near6 (SiC GaN silicon germanium Ge AlN GaAs InP GaP) and buffer near6 (AlInGaN GaN AlN InN AlInN InAlN AlGaN GaAlN InGaN GaInN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 13:56
-	113	active near4 (MQW multiple adj quantum) near12 InGaN and buffer and substrate near6 (SiC GaN silicon germanium Ge AlN GaAs InP GaP) and buffer near6 (AlInGaN GaN AlN InN AlInN InAlN AlGaN GaAlN InGaN GaInN) and (light-emitting light adj emitting).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 13:57
-	94	active near4 (MQW multiple adj quantum) near12 InGaN and buffer and substrate near6 (SiC GaN silicon germanium Ge AlN GaAs InP GaP) and buffer near6 (AlInGaN GaN AlN InN AlInN InAlN AlGaN GaAlN InGaN GaInN) and (light-emitting light adj emitting).ti,ab,clm. and contact adj layer near6 (GaN AlGaN InGaN GaAlN GaInN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 13:58
-	26	active near4 (MQW multiple adj quantum) near12 InGaN and buffer and substrate near6 (SiC GaN silicon germanium Ge AlN GaAs InP GaP) and buffer near6 (AlInGaN GaN AlN InN AlInN InAlN AlGaN GaAlN InGaN GaInN) and (light-emitting light adj emitting).ti,ab,clm. and contact adj layer near6 (GaN AlGaN InGaN GaAlN GaInN) and (conductive adj oxide ITO ZnO cadmium-tin adj oxide ATO antimony-tin adj oxide indium-tin adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 13:59
-	26	active near4 (MQW multiple adj quantum) near12 InGaN and buffer and substrate near6 (SiC GaN silicon germanium Ge AlN GaAs InP GaP) and buffer near6 (AlInGaN GaN AlN InN AlInN InAlN AlGaN GaAlN InGaN GaInN) and (light-emitting light adj emitting).ti,ab,clm. and contact adj layer near6 (GaN AlGaN InGaN GaAlN GaInN) and (conductive adj oxide ITO ZnO cadmium-tin adj oxide ATO antimony-tin adj oxide indium-tin adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 14:01
-	21	active near4 (MQW multiple adj quantum) near6 InGaN and buffer and substrate near6 (SiC GaN silicon germanium Ge AlN GaAs InP GaP) and buffer near6 (AlInGaN GaN AlN InN AlInN InAlN AlGaN GaAlN InGaN GaInN) and (light-emitting light adj emitting).ti,ab,clm. and contact adj layer near6 (GaN AlGaN InGaN GaAlN GaInN) and (conductive adj oxide ITO ZnO cadmium-tin adj oxide ATO antimony-tin adj oxide indium-tin adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 14:02

-	4	active near4 (MQW multiple adj quantum) near6 InGaN and buffer and substrate near6 (SiC GaN silicon germanium Ge AlN GaAs InP GaP) and buffer near6 (AlInGaN GaN AlN InN AlInN InAlN AlGaN GaAlN InGaN GaInN) and (light-emitting light adj emitting).ti,ab,clm. and contact adj layer near6 (GaN AlGaN InGaN GaAlN GaInN) and (conductive adj oxide ITO ZnO cadmium-tin adj oxide ATO antimony-tin adj oxide indium-tin adj oxide) and barrier near6 InGaN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 14:03
-	21	active near4 (MQW multiple adj quantum) near6 InGaN and buffer and substrate near6 (SiC GaN silicon germanium Ge AlN GaAs InP GaP) and buffer near6 (AlInGaN GaN AlN InN AlInN InAlN AlGaN GaAlN InGaN GaInN) and (light-emitting light adj emitting).ti,ab,clm. and contact adj layer near6 (GaN AlGaN InGaN GaAlN GaInN) and (conductive adj oxide ITO ZnO cadmium-tin adj oxide ATO antimony-tin adj oxide indium-tin adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 14:55
-	62	multiple adj quantum adj "well".ti,ab. and light-emitting.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 15:04
-	90	buffer near8 substrate near8 GaAs near8 (AlGaInP AlInGaP GaInAlP GaAlInP InAlAsP InAsAlP)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 15:06
-	18	buffer near4 substrate near4 GaAs near4 (AlGaInP AlInGaP GaInAlP GaAlInP InAlAsP InAsAlP)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/11/06 15:12
-	1	buffer near4 substrate near4 GaAs near4 AlGaN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 16:02
-	1	buffer near4 substrate near4 GaAs near4 (AlInN InAlN GaInN InGaN GaAlN AlGaN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 16:32
-	28	buffer near4 substrate near4 GaAs near4 (AlInP InAlP GaInP InGaP GaAlP AlGaP)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 16:35
-	18	buffer near4 substrate near4 GaAs near4 (AlInP InAlP GaInP InGaP GaAlP AlGaP) and 257/$7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 16:35
-	17	buffer near4 substrate near4 GaAs near4 (AlIn InAlP GaInP InGaP GaAlP AlGaP) and 257/$7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 16:36
-	34	buffer near4 (AlInGaN AlGaInN InAlGaN InAlGaN GaAlInN GaInAlN InGaN GaInN GaAlN AlGaN AlInN InAlN) and substrate near4 GaAs and (multiple adj quantum adj "well" MQW) near4 (INGaN GaInN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/11/06 17:23

-	17	buffer near4 (AlInGaN AlGaInN InAlGaN InAlGaN GaAlInN GaInAlN InGaN GaInN GaAlN AlGaN AlInN InAlN) and substrate near4 GaAs and (multiple adj quantum adj "well" MQW) near4 (INGaN GaInN) and (light-emitting light adj emitting).ti,ab,clm. and 257/$7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 17:38
-	1461	Si-doped adjGaN near12 n-GaN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 17:38
-	6	Si-doped adj GaN near12 n-GaN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 19:36
-	9	II-nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 19:37